



SamHop Microelectronics Corp.

# STM4886

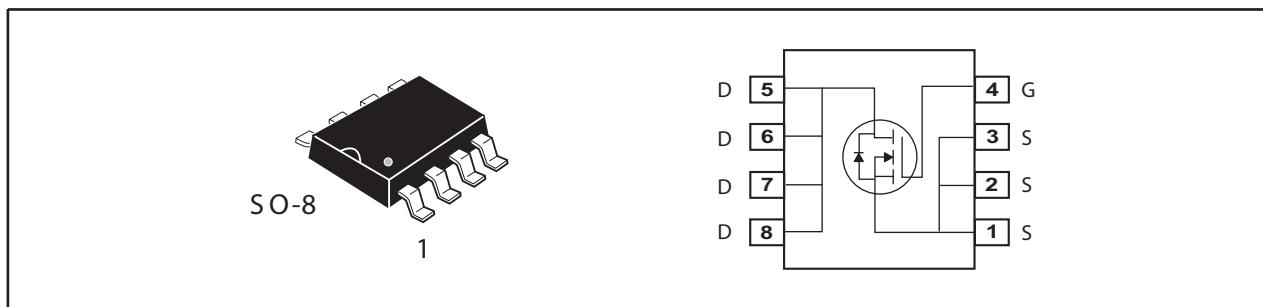
Ver 1.0

## N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DSON</sub> (mΩ) Max
30V	17A	5 @ V <sub>GS</sub> =10V
		8 @ V <sub>GS</sub> =4.5V

### FEATURES

- Super high dense cell design for low R<sub>DSON</sub>.
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous <sup>a</sup>	17	A
I <sub>DM</sub>	-Pulsed <sup>b</sup>	68	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>d</sup>	181	mJ
P <sub>D</sub>	Maximum Power Dissipation <sup>a</sup>	2.5	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

### THERMAL CHARACTERISTICS

R <sub>θ JA</sub>	Thermal Resistance, Junction-to-Ambient <sup>a</sup>	50	°C/W
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Details are subject to change without notice.

Mar,24,2008

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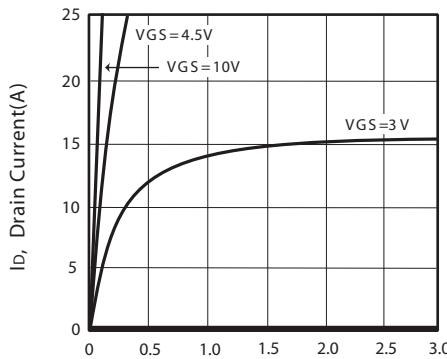
## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V , ID=250uA	30			V
IDSS	Zero Gate Voltage Drain Current	VDS=24V , VGS=0V			1	uA
IGSS	Gate-Body Leakage Current	VGS= ±20V , VDS=0V			±100	nA
<b>ON CHARACTERISTICS</b>						
VGS(th)	Gate Threshold Voltage	VDS=VGS , ID=250uA	1	1.7	3	V
RDS(ON)	Drain-Source On-State Resistance	VGS=10V , ID=17A		3.8	5	m ohm
		VGS=4.5V , ID=13.5A		5.8	8	m ohm
gFS	Forward Transconductance	VDS=15V , ID=17A		20		S
<b>DYNAMIC CHARACTERISTICS</b> <sup>c</sup>						
Ciss	Input Capacitance	VDS=15V,VGS=0V f=1.0MHz		2500		pF
Coss	Output Capacitance			640		pF
CRSS	Reverse Transfer Capacitance			440		pF
<b>SWITCHING CHARACTERISTICS</b> <sup>c</sup>						
tD(ON)	Turn-On Delay Time	VDD=15V ID=17A VGS=10V RGEN=6 ohm		52		ns
tr	Rise Time			85		ns
tD(OFF)	Turn-Off Delay Time			82		ns
tf	Fall Time			65		ns
Qg	Total Gate Charge	VDS=15V, ID=17A, VGS=10V		58		nC
		VDS=15V, ID=17A, VGS=4.5V		28		nC
Qgs	Gate-Source Charge	VDS=15V, ID=17A, VGS=10V		5.4		nC
Qgd	Gate-Drain Charge			17		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b> <sup>c</sup>						
VSD	Diode Forward Voltage	VGS=0V, IS=17A		0.73	1.2	V
<b>Notes</b>						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
c.Guaranteed by design, not subject to production testing.						
d.Starting TJ=25°C,L=1.25mH,RG=25Ω,IAS=17A,VDD = 30V.(See Figure13)						

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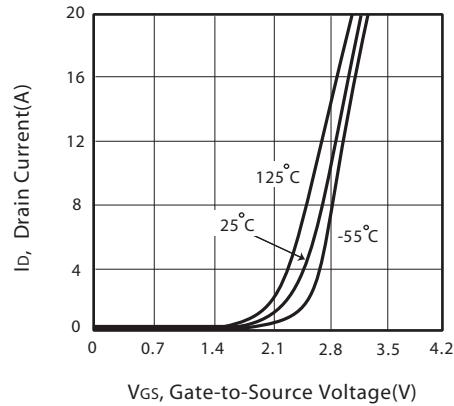
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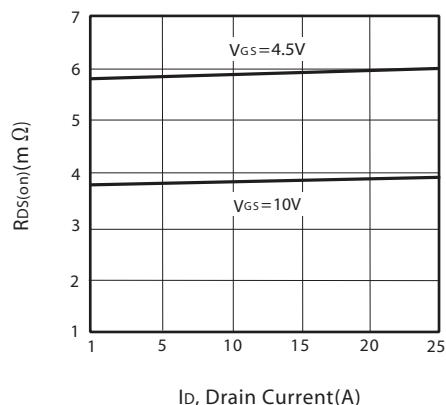
$V_{DS}$ , Drain-to-Source Voltage(V)

Figure 1. Output Characteristics

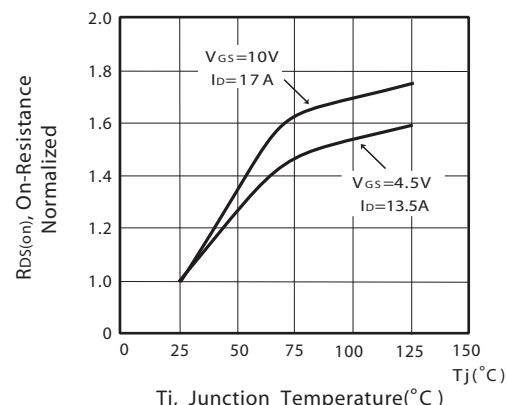


$V_{GS}$ , Gate-to-Source Voltage(V)

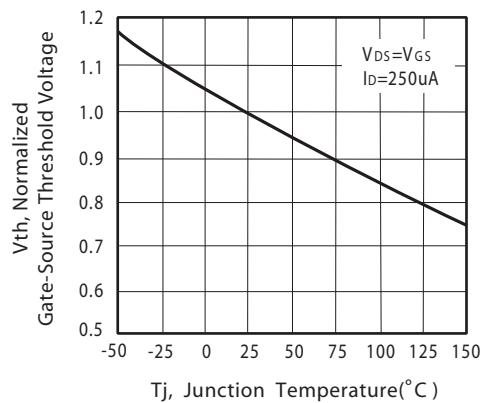
Figure 2. Transfer Characteristics



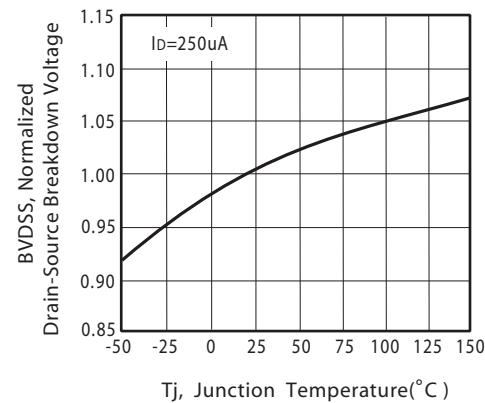
$V_{GS}$ , Gate-to-Source Voltage  
 $I_D$ , Drain Current



$V_{GS}$ , Gate-to-Source Voltage  
 $I_D$ , Drain Current  
 $T_j$ , Junction Temperature



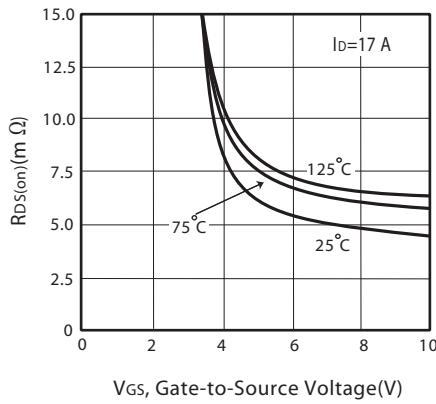
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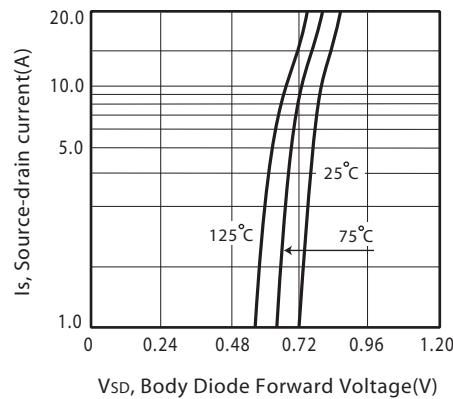
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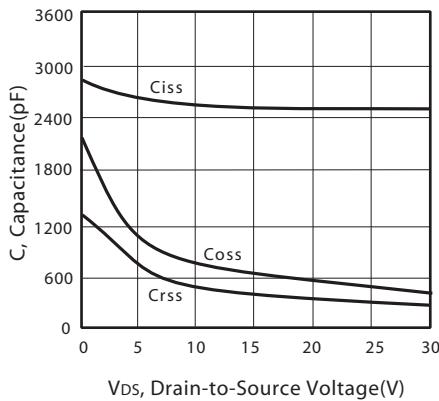
V<sub>GS</sub>, Gate-to-Source Voltage(V)

Figure 7. On-Resistance vs.  
Gate-Source Voltage



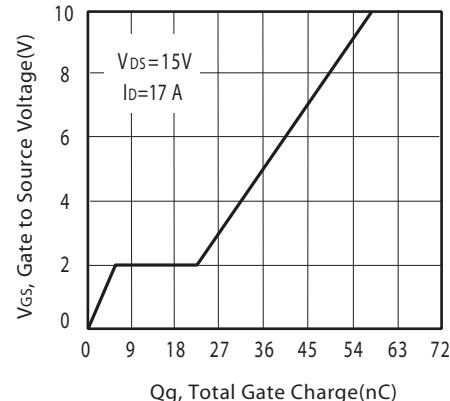
V<sub>SD</sub>, Body Diode Forward Voltage(V)

Figure 8. Body Diode Forward Voltage  
Variation with Source Current



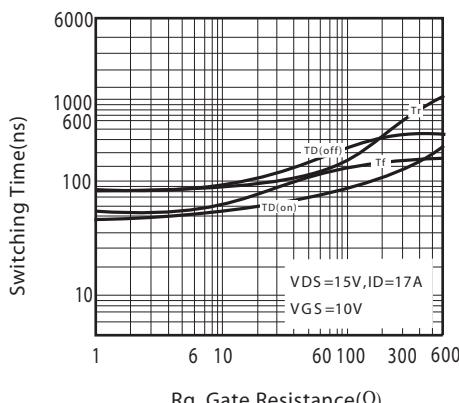
V<sub>DS</sub>, Drain-to-Source Voltage(V)

Figure 9. Capacitance



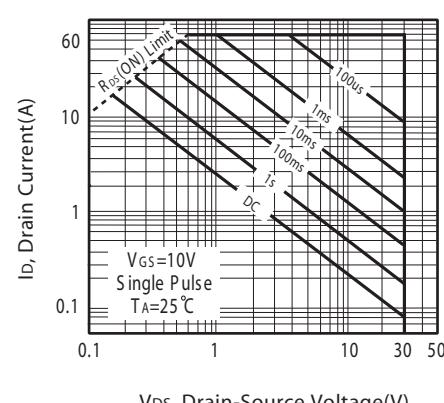
Q<sub>g</sub>, Total Gate Charge(nC)

Figure 10. Gate Charge



R<sub>g</sub>, Gate Resistance(Ω)

Figure 11. switching characteristics

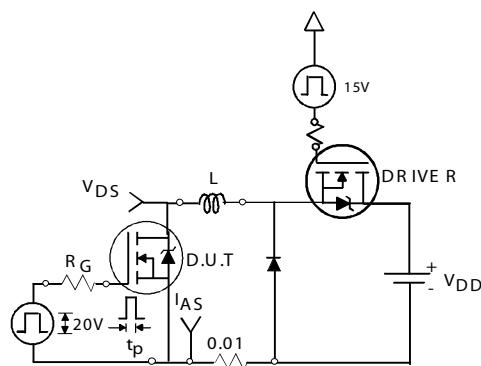


V<sub>DS</sub>, Drain-Source Voltage(V)

Figure 12. Maximum Safe Operating Area

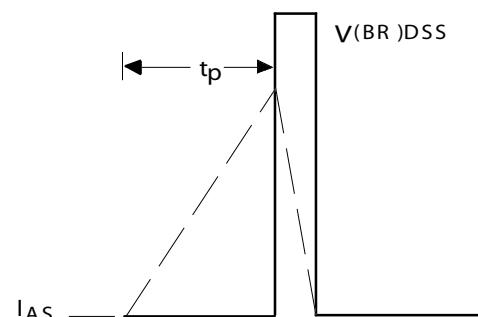
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Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

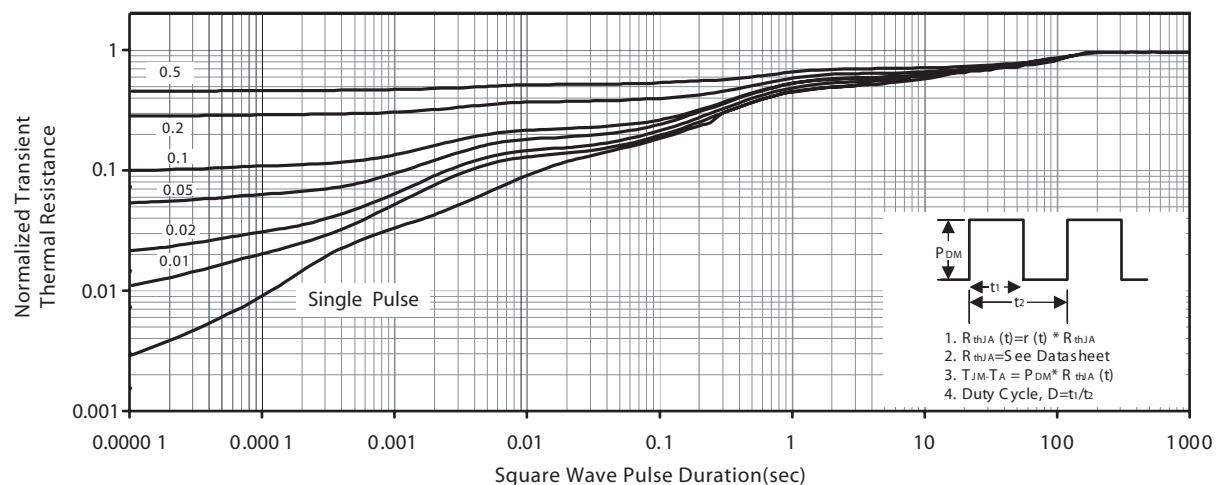
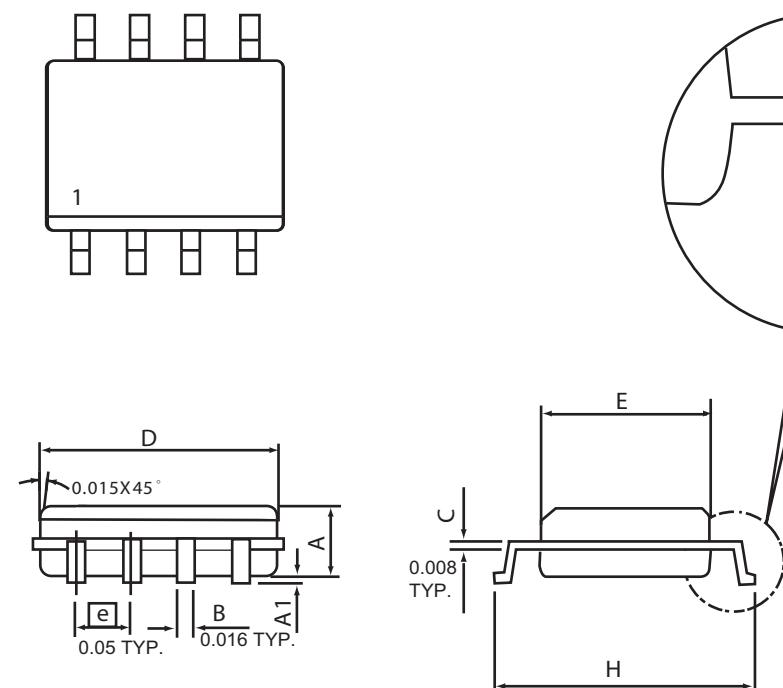


Figure 14. Normalized Thermal Transient Impedance Curve

## PACKAGE OUTLINE DIMENSIONS

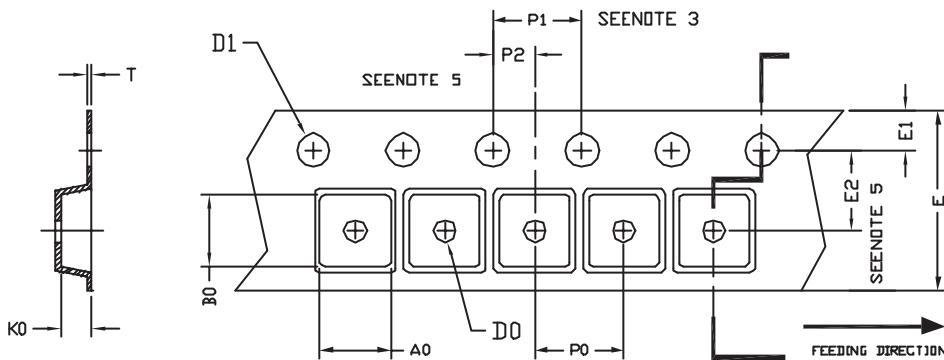
SO-8



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

## SO-8 Tape and Reel Data

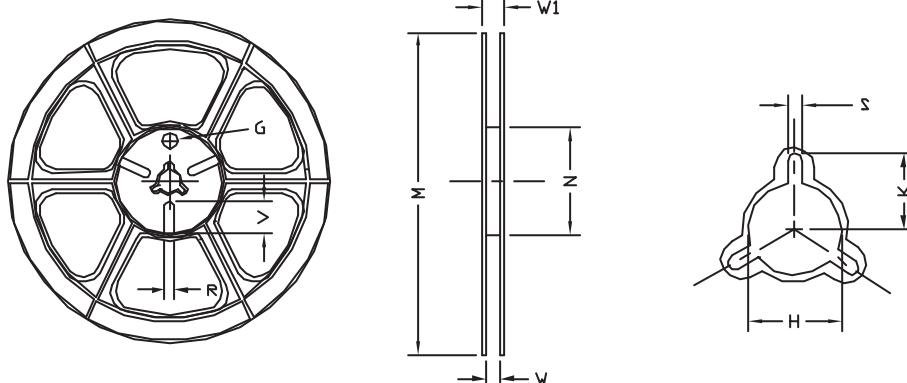
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ $+ 0.1$ $- 0.0$	12.0 $\pm 0.3$	1.75	5.5 $\pm 0.05$	8.0	4.0	2.0 $\pm 0.05$	0.3 $\pm 0.05$

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 $\pm 1$	62 $\pm 1.5$	12.4 $+ 0.2$	16.8 $- 0.4$	$\phi 12.75$ $+ 0.15$	---	2.0 $\pm 0.15$	---	---	---